

Japanese Unexamined Patent Application Publication No. 3-238863

**SPECIFICATION <EXCERPT>**

In FIG. 1, on a upper-side position of photoelectric conversion N<sup>-</sup> layer 4 of the base film 9 having a thickness of several  $\mu$  m to 10  $\mu$  m, a circular or square oxide film 12 made of SiO<sub>2</sub> as a transparent film by the plasma CVD method. Then tetraethoxysilane (hereinafter, referred to as TEOS) that is organic silane is deposited on the oxide film 12 to form light-receiving lens 13 having a convex lens shape.